

Silicon N-Channel Power MOSFET

General Description :

GL8N50FA9*, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

Features :

- Fast Switching
- Low ON Resistance($R_{ds(on)} \leq 0.75\Omega$)
- Low Gate Charge (Typical Data:29nC)
- Low Reverse transfer capacitances(Typical:25pF)
- 100% Single Pulse avalanche energy Test

Applications:

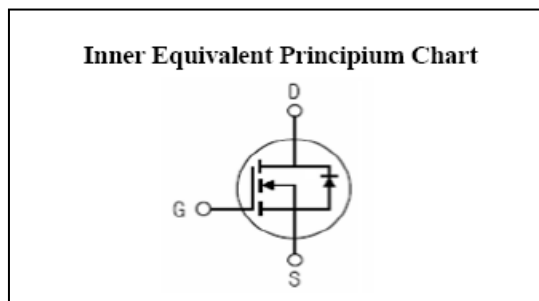
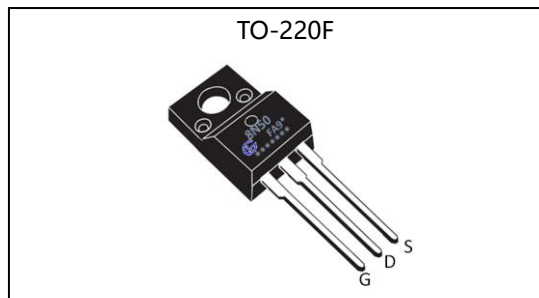
- Power switch circuit of adaptor and charger

Absolute ($T_c=25^\circ\text{C}$ unless otherwise specified) :

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	500	V
I_D	Continuous Drain Current	8	A
	Continuous Drain Current $T_c=100^\circ\text{C}$	5.7	A
I_{DM}^{a1}	Pulsed Drain Current	32	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	620	mJ
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	45	W
	Derating Factor above 25°C	0.36	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150 , -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

V_{DSS}	500	V
I_D	8	A
$P_D(T_c=25^\circ\text{C})$	45	W
$R_{DS(ON),TYP.}$	0.6	Ω



**GL8N50FA9***

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*Silicon N-Channel Power MOSFET***Thermal Characteristics**

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.78	°C/ W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	°C/ W

Electrical Characteristics ($T_c = 25^{\circ}\text{C}$ unless otherwise specified) :

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	500	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=500V, V_{GS}=0V, T_a=25^{\circ}\text{C}$	--	--	1.0	μA
		$V_{DS}=400V, V_{GS}=0V, T_a=125^{\circ}\text{C}$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=4.5A$	--	0.6	0.75	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
g_{fs}	Forward Trans conductance	$V_{DS}=15V, I_D=4.5A$	--	6.2	--	S
Pulse width<380 μs ; duty cycle<2%.						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V$ $f=1.0\text{MHz}$	--	850	--	pF
C_{oss}	Output Capacitance		--	150	--	
C_{rss}	Reverse Transfer Capacitance		--	25	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=8A, V_{DD}=250V$ $V_{GS}=10V, R_g=25\Omega$	--	65	--	ns
t_r	Rise Time		--	50	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	100	--	
t_f	Fall Time		--	65	--	
Q_g	Total Gate Charge	$I_D=8A, V_{DD}=400V$ $V_{GS}=10V$	--	29	--	nC
Q_{gs}	Gate to Source Charge		--	4.3	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	13	--	

**Silicon N-Channel Power MOSFET**

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_{SD}	Continuous Source Current (Body Diode)		--	--	8	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	32	A
V_{SD}	Diode Forward Voltage	$I_S=8A, V_{GS}=0V$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$I_S=8A, T_J=25^{\circ}C$	--	330	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/\mu s, V_{GS}=0V$	--	2.5	--	μC

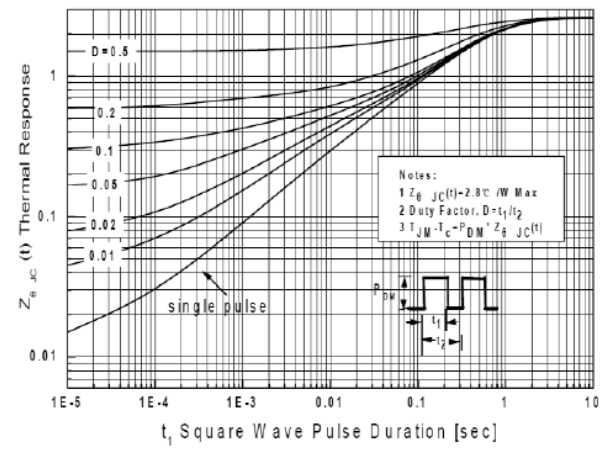
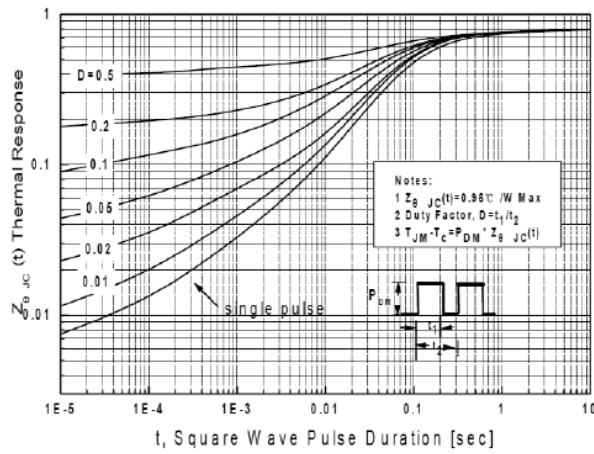
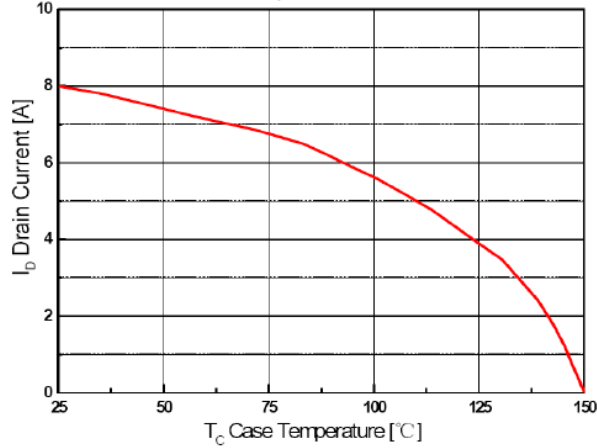
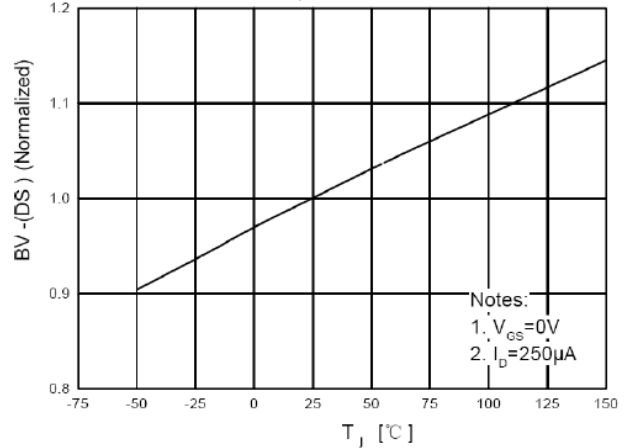
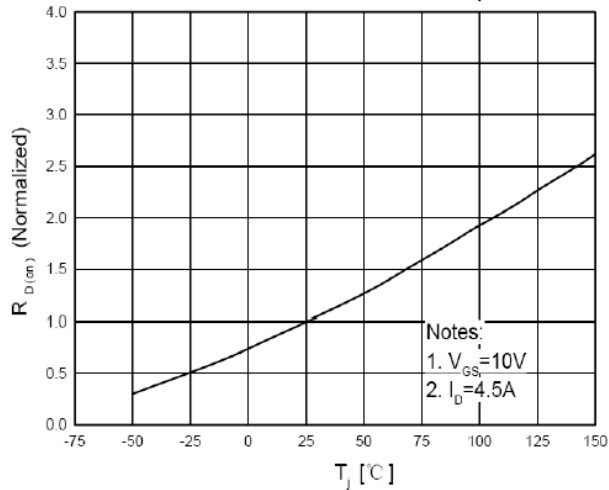
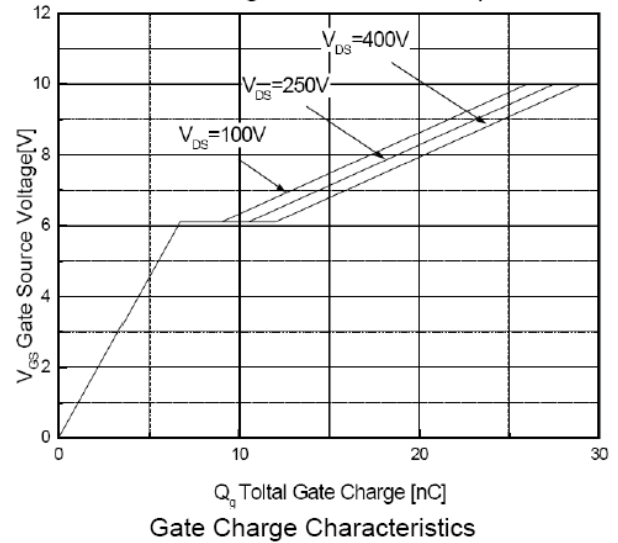
a1 : Repetitive rating; pulse width limited by maximum junction temperature

a2 : $L=10mH$, $I_D=11.1A$, Start $T_J=25^{\circ}C$

a3 : $I_{SD}=8A, di/dt \leq 100A/\mu s, V_{DD} \leq BV_{DS}$, Start $T_J=25^{\circ}C$

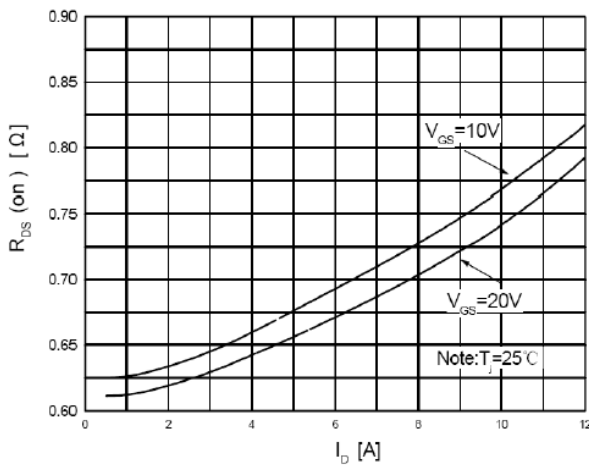
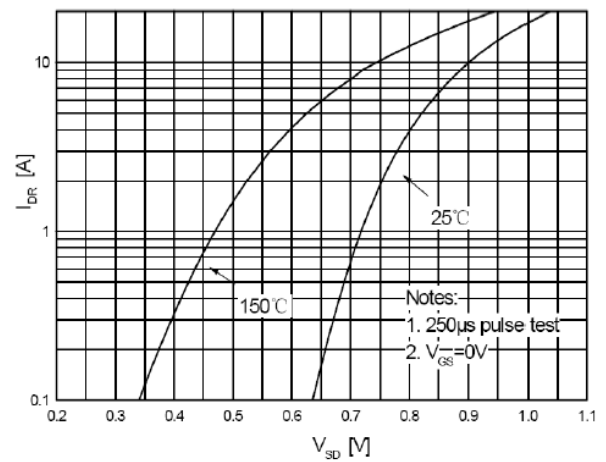
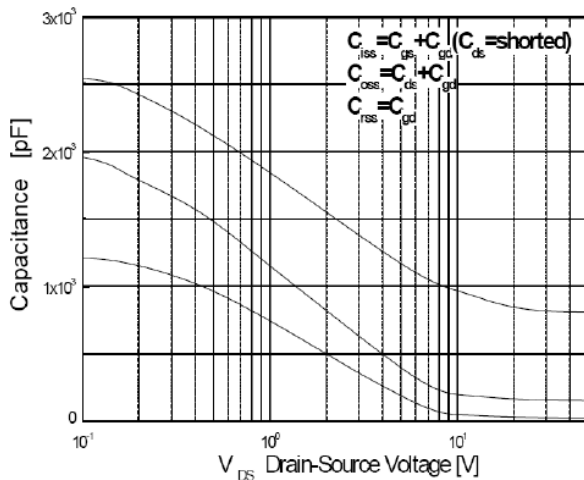
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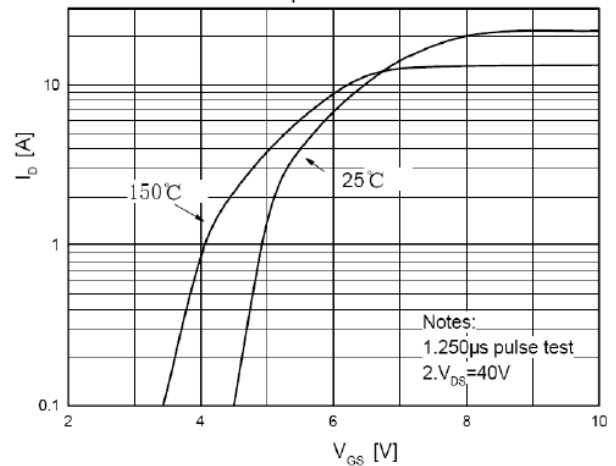
Silicon N-Channel Power MOSFET**Characteristics Curve :****Transient Thermal Response Curve For TO-220****Transient Thermal Response Curve For TO-220F****Maximum Drain Current vs. Case Temperature****Breakdown Voltage Variation vs. Temperature****On-Resistance Variation vs. Temperature**

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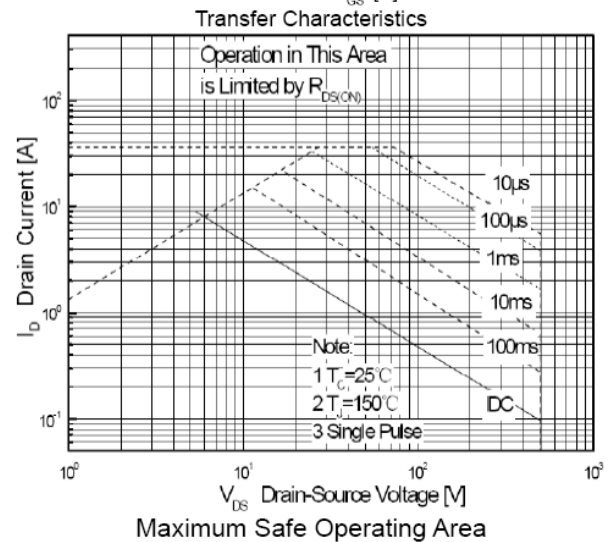
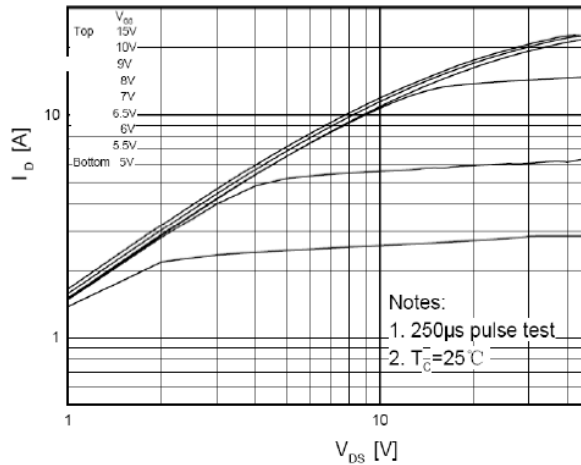
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Body Diode Forward Voltage Variation vs. Source Current and Temperature



On-Resistance Variation vs. Drain Current and Gate Voltage



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